Supplementary Information

Suppressing current leakage and voltage drift in indium-modified electrical switching devices

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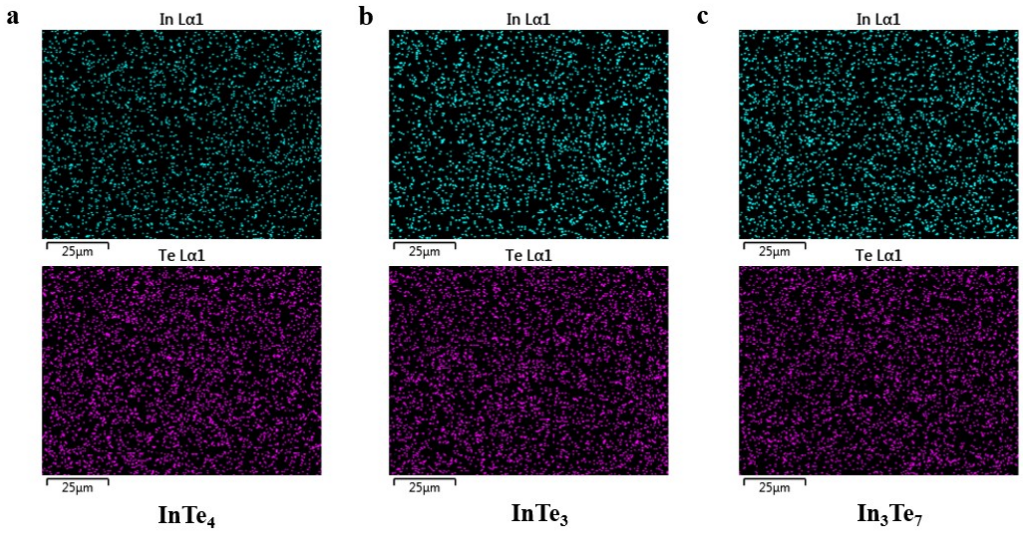

Fig. S1. EDS mappings of In, Te for $InTe_4$, $InTe_3$, and In_3Te_7 films.

Table S1. The weight percentage and atomic percentage of In and Te obtained from the EDS mappings			
$InTe_4$	**Weight%**	**Wt% Sigma**	**Atom%**
In	19.41	0.36	**21.1**
Te	80.56	0.36	**78.9**
$InTe_3$	**Weight%**	**Wt% Sigma**	**Atom%**
In	22.33	0.36	**24.21**
Te	77.67	0.36	**75.79**
In_3Te_7	**Weight%**	**Wt% Sigma**	**Atom%**
In	27.84	0.36	**30.00**
Te	72.16	0.36	**70.00**

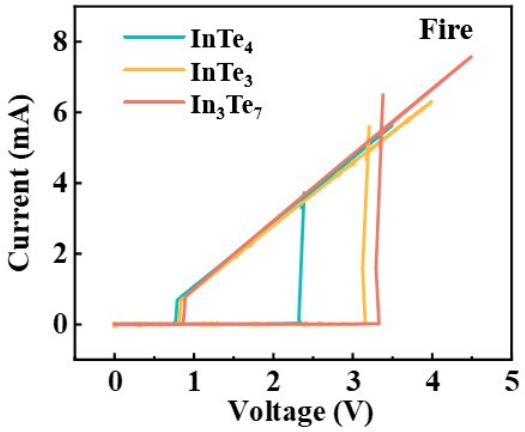

Fig. S2. Firing I–V characteristics of $InTe_4$, $InTe_3$, and In_3Te_7 OTS devices.

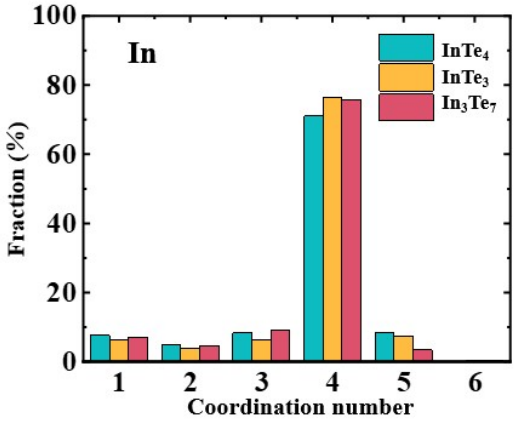

Fig. S3. Coordination numbers (CN) of In atoms in a-$InTe_4$, a-$InTe_3$, and a-In_3Te_7.

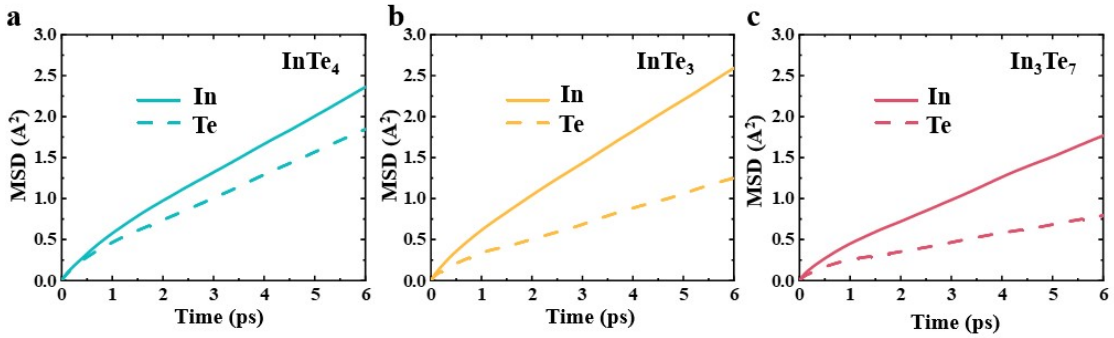

Fig. S4. Mean square displacement (MSD) of In and Te atoms in a-$InTe_4$, a-$InTe_3$, and a-In_3Te_7.